

2SJ76, 2SJ77, 2SJ78, 2SJ79

Silicon P Channel MOS FET

REJ03G0122-0200
(Previous: ADE-208-1179)
Rev.2.00
Sep 07, 2005

Description

High frequency and low frequency power amplifier, high speed power switching

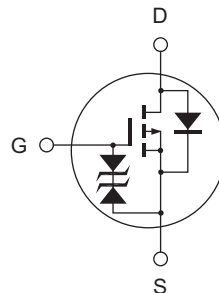
Complementary pair with 2SK213, 2SK214, 2SK215, 2SK216

Features

- Suitable for direct mounting
- High forward transfer admittance
- Excellent frequency response
- Enhancement-mode

Outline

RENESAS Package code: PRSS0004AC-A
(Package name: TO-220AB)



1. Gate
2. Source (Flange)
3. Drain

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	2SJ76	-140	V
	2SJ77	-160	
	2SJ78	-180	
	2SJ79	-200	
Gate to source voltage	V _{GSS}	±15	V
Drain current	I _D	-500	mA
Body to drain diode reverse drain current	I _{DR}	-500	mA
Channel dissipation	P _{ch}	1.75	W
	P _{ch} ^{Note 1}	30	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-45 to +150	°C

Note: 1. Value at Tc = 25°C

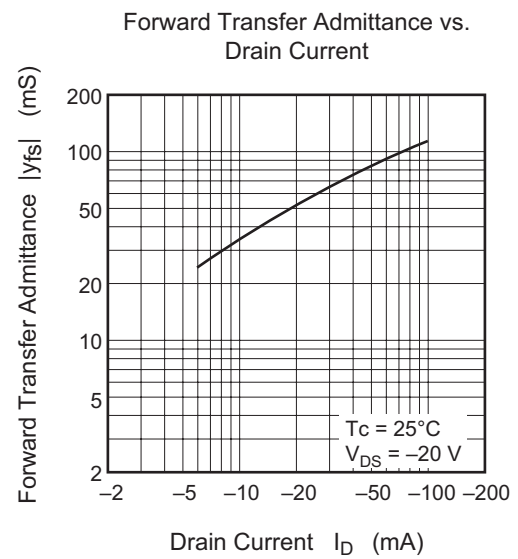
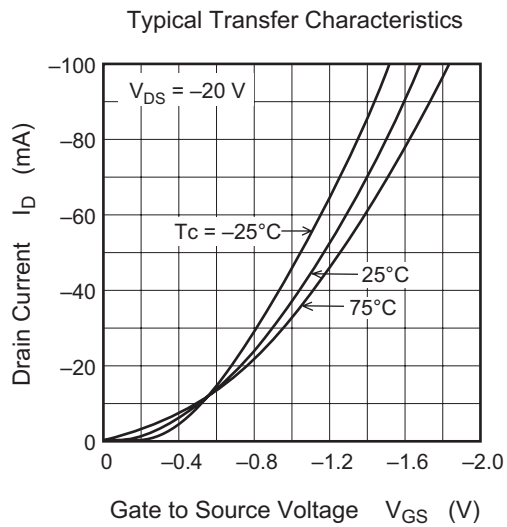
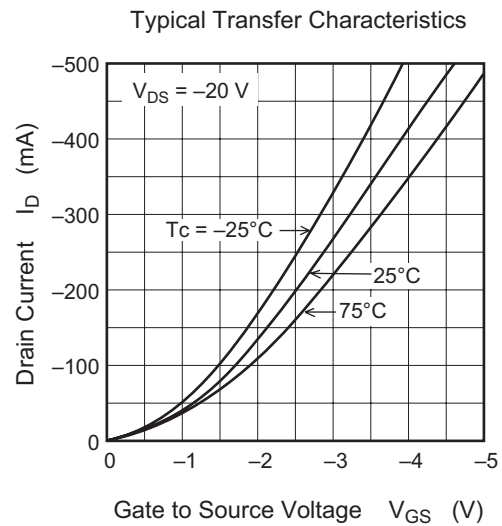
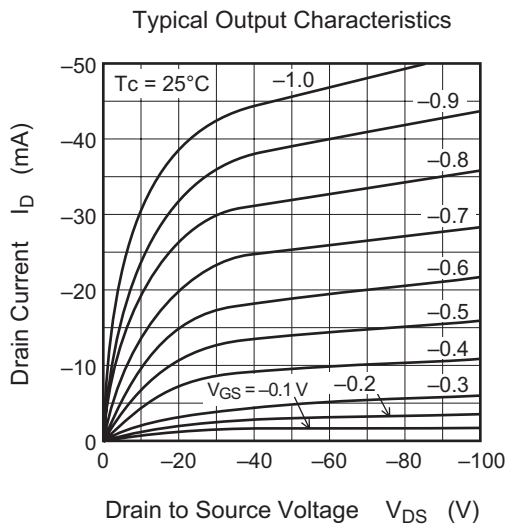
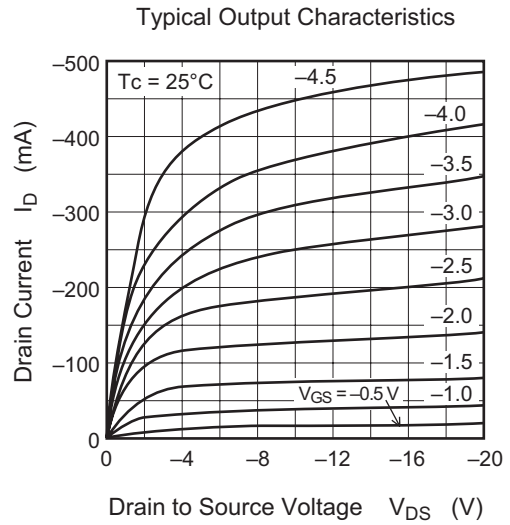
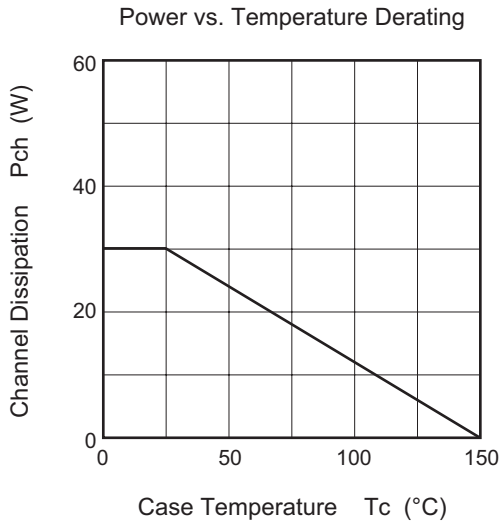
Electrical Characteristics

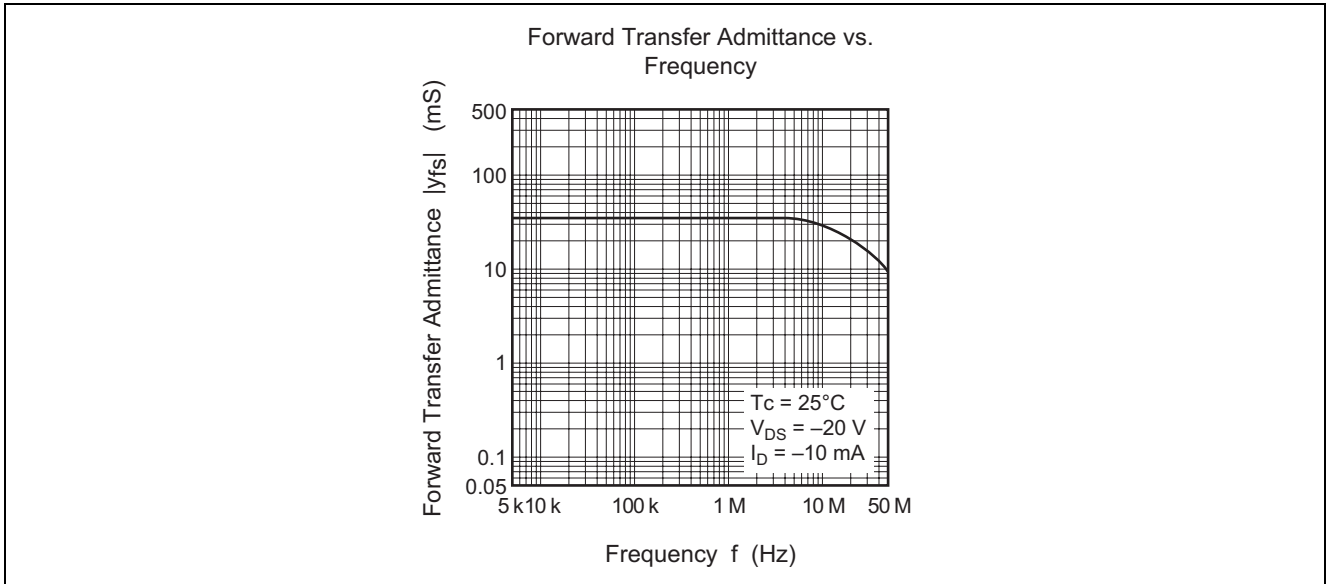
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	2SJ76	-140	—	—	V	V _{GS} = 2 V, I _D = -1 mA
	2SJ77	-160	—	—	V	
	2SJ78	-180	—	—	V	
	2SJ79	-200	—	—	V	
Gate to source breakdown voltage	V _{(BR)GSS}	±15	—	—	V	I _G = ±10 μA, V _{DS} = 0
Gate to source cutoff voltage	V _{GS(on)}	-0.2	—	-1.5	V	I _D = -10 mA, V _{DS} = -10 V ^{Note 2}
Drain to source saturation voltage	V _{DS(sat)}	—	—	-2.0	V	I _D = -10 mA, V _{GS} = 0 ^{Note 2}
Forward transfer admittance	y _{fs}	20	35	—	mS	I _D = -10 mA, V _{DS} = -20 V ^{Note 2}
Input capacitance	C _{iss}	—	120	—	pF	V _{DS} = -10 V, I _D = -10 mA, f = 1 MHz
Reverse transfer capacitance	C _{rss}	—	4.8	—	pF	

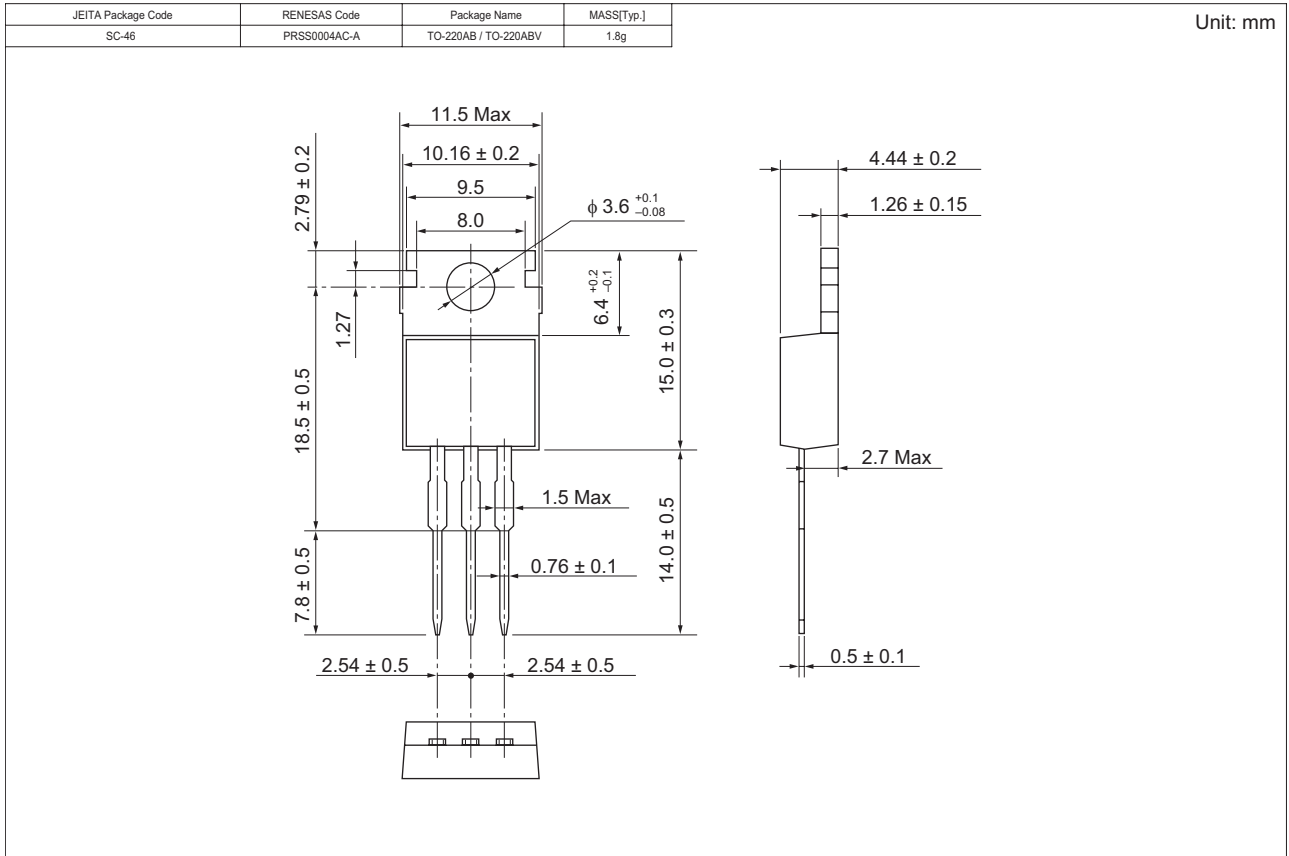
Note: 2. Pulse test

Main Characteristics





Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SJ76-E	500 pcs	Box (Sack)
2SJ77-E	500 pcs	Box (Sack)
2SJ78-E	500 pcs	Box (Sack)
2SJ79-E	500 pcs	Box (Sack)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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